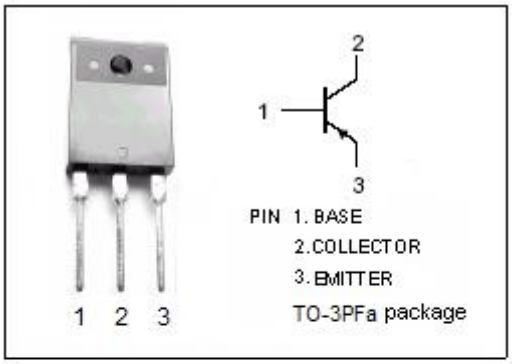
isc Silicon PNP Power Transistor — 2SB966

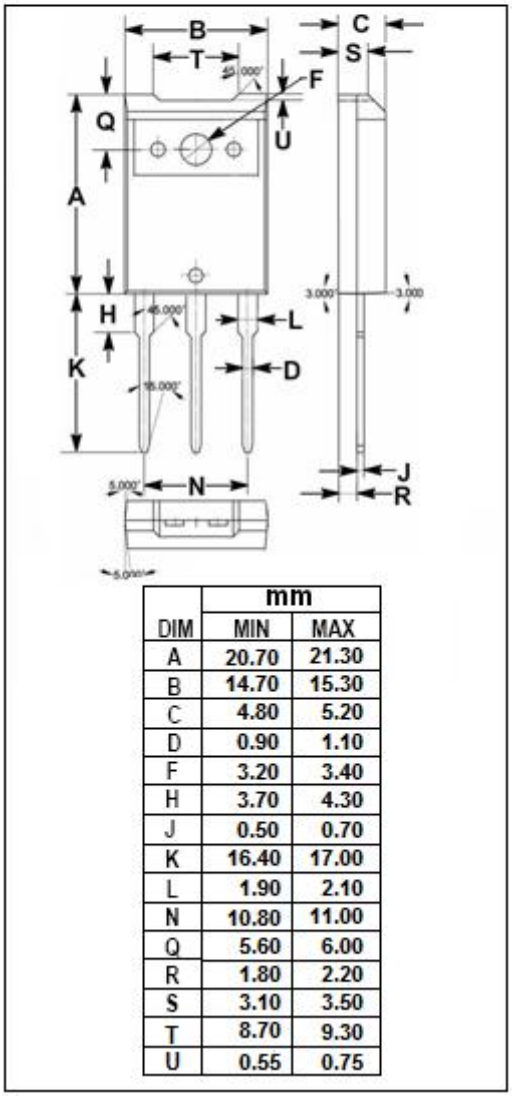


DESCRIPTION

- Low Collector Saturation Voltage
  : $V_{CE(sat)}$= -0.65V(Typ)@I_C= -5.0A
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -120V(Min)
- Complement to Type 2SD1289
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Audio frequency power amplifier applications



DIM	mm MIN	MAX
A	20.70	21.30
B	14.70	15.30
C	4.80	5.20
D	0.90	1.10
F	3.20	3.40
H	3.70	4.30
J	0.50	0.70
K	16.40	17.00
L	1.90	2.10
N	10.80	11.00
Q	5.60	6.00
R	1.80	2.20
S	3.10	3.50
T	8.70	9.30
U	0.55	0.75

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-8	A
I_{CP}	Collector Current-Pulse	-12	A
P_C	Total Power Dissipation @ Tc=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

isc Silicon PNP Power Transistor 2SB966

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{CE(sat)}$NOTE	Collector-Emitter Saturation Voltage	I_C= -5.0A; I_B= -0.5A		-0.65	-1.5	V
$V_{BE(sat)}$NOTE	Base-Emitter Saturation Voltage	I_C= -5.0A; I_B= -0.5A		-1.25	-2.0	V
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-50	μA
I_{CBO}	Collector Cutoff Current	V_{CB}= -120V; I_E= 0			-50	μA
h_{FE1}NOTE	DC Current Gain	I_C= -1A; V_{CE}= -5V	60		320	
h_{FE2}NOTE	DC Current Gain	I_C= -50mA; V_{CE}= -5V	40			
fT	Transition frequency	V_{CE}=-5V ,I_C=-1A		65		MHz
Cob	Collector output capacitance	V_{CB}=-10V ,I_E=0,f=1MHz		200		pF

NOTE:Pulse test PW≤350us,duty cycle ≤2%

◆ **h_{FE1} Classifications**

R	Q	P
60-120	100-200	160-320